

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
28 April 2022 (28.04.2022)



(10) International Publication Number
WO 2022/086871 A1

(51) International Patent Classification:

H01L 21/02 (2006.01) C23C 16/509 (2006.01)
H01L 21/311 (2006.01) H01L 21/033 (2006.01)
C23C 16/26 (2006.01)

(21) International Application Number:

PCT/US2021/055464

(22) International Filing Date:

18 October 2021 (18.10.2021)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

17/077,926 22 October 2020 (22.10.2020) US

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(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM,

(54) Title: **HARDMASK TUNING BY ELECTRODE ADJUSTMENT**

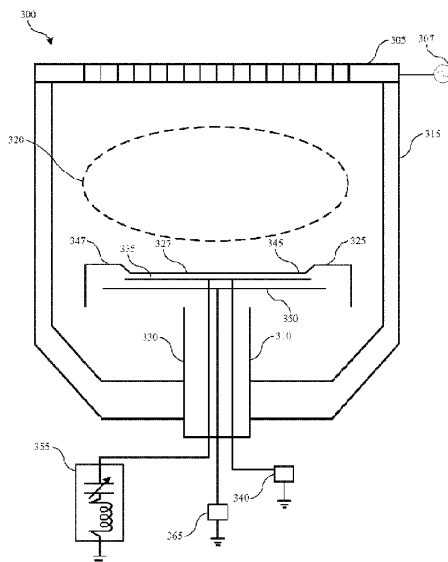


FIG. 3

(57) Abstract: Exemplary processing methods may include forming a plasma of a deposition precursor in a processing region of a semiconductor processing chamber. The methods may include adjusting a variable capacitor within 20% of a resonance peak. The variable capacitor may be coupled with an electrode incorporated within a substrate support on which a substrate is seated. The methods may include depositing a material on the substrate.

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TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW,
KM, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*